



DSS4240T

LOW V_{CE(SAT)} NPN SURFACE MOUNT TRANSISTOR

Features

- Ideal for Medium Power Amplification and Switching
- Ultra Low Collector-Emitter Saturation Voltage
- Complimentary NPN Type Available (DSS5240T)
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)

Mechanical Data

Case: SOT-23

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- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)



B E Device Schematic

Maximum Ratings $@T_A = 25^{\circ}C$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	40	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	3	A
Continuous Collector Current	lc	2	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 3) @ T _A = 25°C	PD	600	mW
Thermal Resistance, Junction to Ambient Air (Note 3) @ T _A = 25°C	$R_{ extsf{ heta}JA}$	209	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

3. Device mounted on FR-4 PCB with minimum recommended pad layout, which can be found on our website at

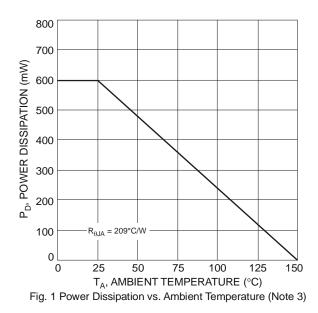
http://www.diodes.com/datasheets/ap02001.pdf.

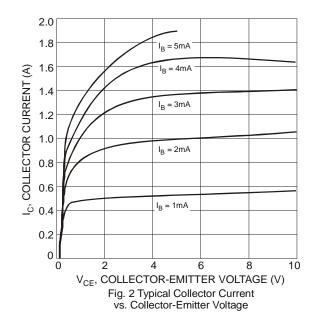


Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions	
OFF CHARACTERISTICS						·	
Collector-Base Breakdown Voltage	V _{(BR)CBO}	40		_	V	$I_C = 100 \mu A$	
Collector-Emitter Breakdown Voltage (Note 4)	V _{(BR)CEO}	40		_	V	$I_{C} = 10 \text{mA}$	
Emitter-Base Breakdown Voltage	V _{(BR)EBO}	5	_	_	V	I _E = 100μA	
Collector-Base Cutoff Current		_	_	100	nA	$V_{CB} = 30V, I_E = 0$	
Collector-base Cuton Current	I _{CBO}	_		50	μA	$V_{CB} = 30V, I_E = 0, T_A = 150^{\circ}C$	
Emitter-Base Cutoff Current	I _{EBO}	_	_	100	nA	$V_{EB} = 4V, I_{C} = 0$	
ON CHARACTERISTICS (Note 4)							
		350		_		$V_{CE} = 2V, I_{C} = 0.1A$	
DC Current Gain	h	300	_	—		$V_{CE} = 2V, I_{C} = 0.5A$	
	h _{FE}	300		_		$V_{CE} = 2V, I_{C} = 1A$	
		150	_	_		$V_{CE} = 2V, I_C = 2A$	
		_	_	70		$I_{C} = 100 \text{mA}, I_{B} = 1 \text{mA}$	
		_	30	100]	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$	
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	_	_	180	mV	I _C = 750mA, I _B = 15mA	
		_		180		$I_{C} = 1A, I_{B} = 50mA$	
		_	_	320		$I_{C} = 2A, I_{B} = 200 \text{mA}$	
Equivalent On-Resistance	R _{CE(SAT)}	_	60	200	mΩ	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$	
Base-Emitter Saturation Voltage	V _{BE(SAT)}	_	_	1.1	V	$I_{\rm C} = 2A, I_{\rm B} = 200 {\rm mA}$	
Base-Emitter Turn-on Voltage	V _{BE(ON)}	_		0.75	V	$V_{CE} = 2V, I_{C} = 100 \text{mA}$	
SMALL SIGNAL CHARACTERISTICS	· · · ·			•	•	·	
Transition Frequency	f _T	100	_		MHz	$V_{CE} = 10V, I_C = 100mA,$ f = 100MHz	
Output Capacitance	Cob	_		20	pF	V _{CB} = 10V, f = 1MHz	

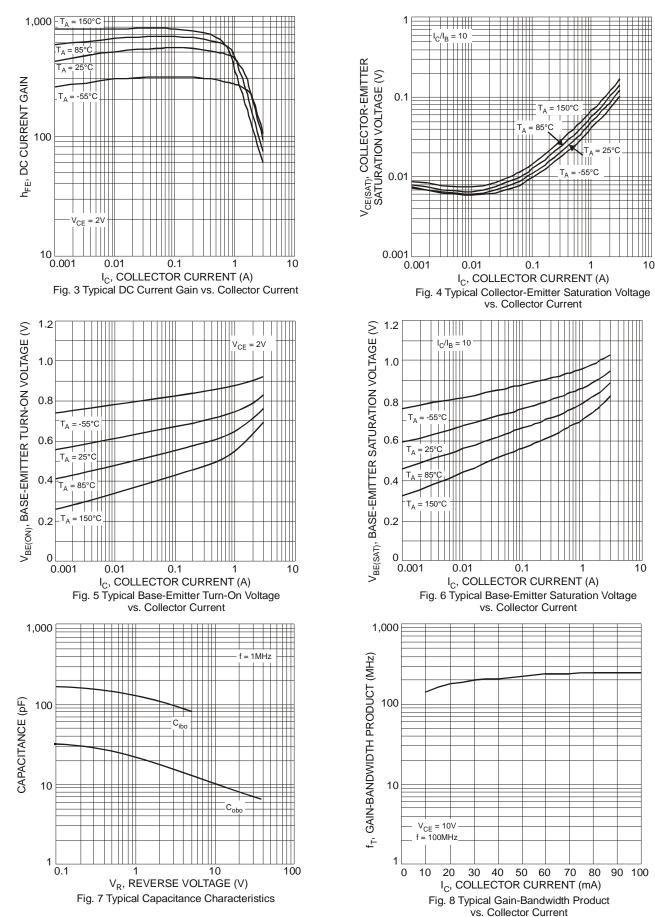
Notes: 4. Measured under pulsed conditions. Pulse width = 300μ s. Duty cycle $\leq 2\%$.







DSS4240T



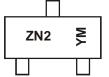


Ordering Information (Note 6)

Bort Number Cooo Book	
Part Number Case Pack	aging
DSS4240T-7 SOT-23 3000/Ta	pe & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

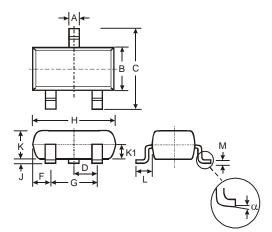


ZN2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

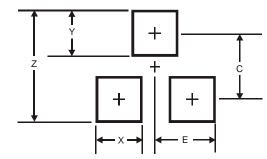
Year	2008		2009	2010		2011	2012		2013	2014		2015
Code	V		W	Х		Y	Z		А	В		С
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



SOT-23					
Dim	Min	Max	Тур		
Α	0.37	0.51	0.40		
В	1.20	1.40	1.30		
С	2.30	2.50	2.40		
D	0.89	1.03	0.915		
F	0.45	0.60	0.535		
G	1.78	2.05	1.83		
Н	2.80	3.00	2.90		
J	0.013	0.10	0.05		
К	0.903	1.10	1.00		
K1	-	-	0.400		
L	0.45	0.61	0.55		
М	0.085	0.18	0.11		
α	0°	8°	-		
All Dimensions in mm					

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
Х	0.8
Y	0.9
С	2.0
E	1.35



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